

MBR30100CT MBRB30100CT MBR30100CT-1



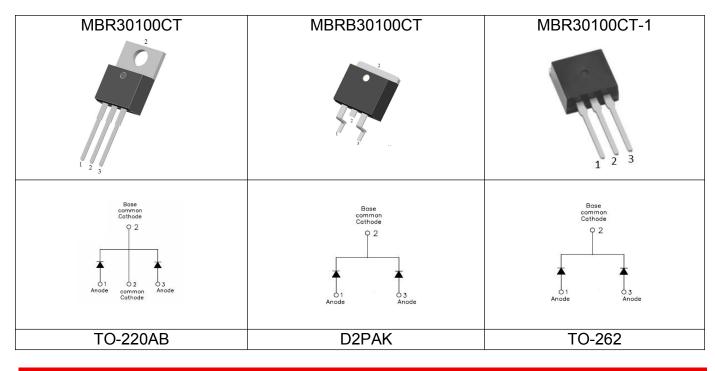
MBR30100CT/MBRB30100CT/MBR30100CT-1 SCHOTTKY RECTIFIER

Features

- 175 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=133°C, rectangular wave form	15(Per Leg) 30(Per Device)	A
Peak Repetitive Forward Current(Per Leg)	I _{FRM}	Rated V _R square wave, 20KHz T _C = 133°C	20	А
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	200	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 15 A, Pulse, T」 = 25 °C @ 30 A, Pulse, T」 = 25 °C	0.78 0.90	0.85 1.05	V
	V _{F2}	@ 15 A, Pulse, T」 = 125 °C @ 30 A, Pulse, T」 = 125 °C	0.67 0.77	0.70 0.85	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.003	1.00	mA
	I _{R2}	$@V_R = rated V_R$ T _J = 125 °C	2	15.0	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	380	500	pF
Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 $\mu s, \ duty \ cycle < 2\%$

Thermal-Mechanical Specifications:

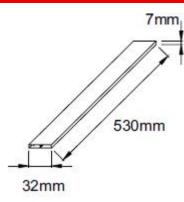
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{0JC}	DC operation	1.5	°C/W
Typical Thermal Resistance Junction to Case	R _{0JA}	DC operation	50	°C/W
Typical Thermal Resistance, Case to Heat Sink	R _{0CS}	Mounting surface, smooth and greased	0.50	°C/W
Case Style	TO-220AB D ² PAK TO-262			

Tube Specification

Device	Package	Weight	Shipping
MBR30100CT	TO-220AB	1.8g	50pcs / tube
MBRB30100CT	D ² PAK	1.85g	800pcs / reel
MBR30100CT-1	TO-262	1.85g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

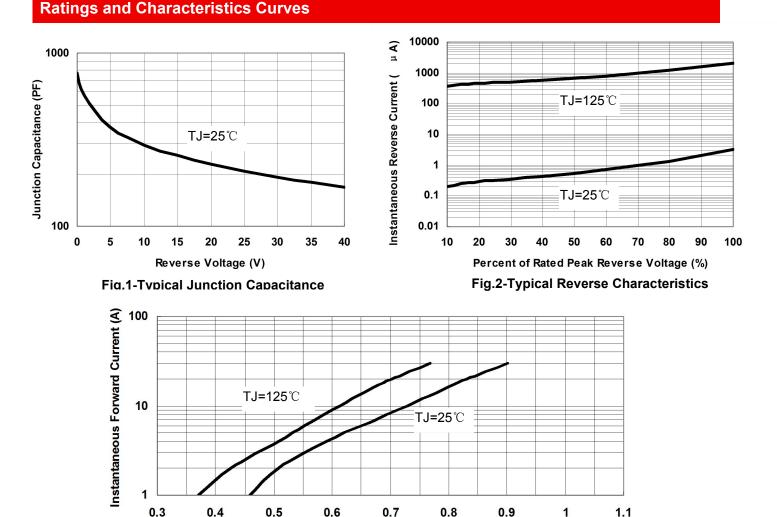
Tube Specification(TO-220AB/TO-262)





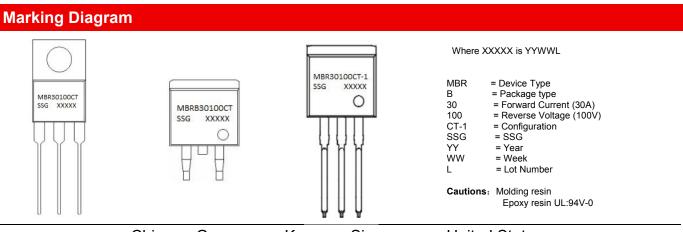
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Forward Voltage Drop (V)

Fig.3-Typical Instantaneous Forward Voltage Characteristics



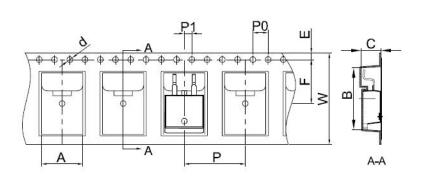
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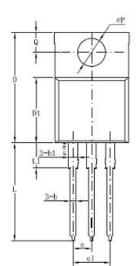
Carrier Tape Specification D2PAK

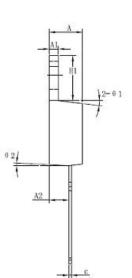


Symbol	Millimeters		
	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

Mechanical Dimensions TO-220AB



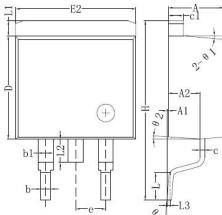




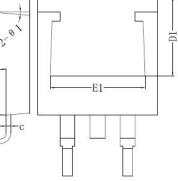
Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
е		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ΦΡ	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7 °		
Θ2		3°		
Θ3		4 °		



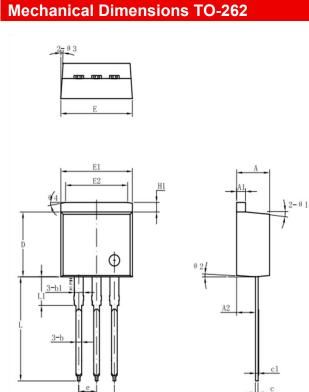
Mechanical Dimensions D²PAK



-2-₀₃



Symbol	Millimeters			
-	Min. Typical		Max.	
Α	4.47	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.50	8.70	8.90	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.31	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.74	
L1	1.12	1.27	1.42	
L2	1.30		2.20	
L3		0.25BSC		
e	0	-	8°	
e1		5°		
e2		4°		
e3		4°		



Cumb al	Millimeters			
Symbol	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.55	8.70	8.85	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.18	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.70	
L1	1.17	1.27	1.40	
L2			2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4°		
e3		4 °		

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